

DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name;

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

CVD Tantalum compounds for FET gate electrodes

the specification of which (check one)

☒ is attached hereto.

☐ was filed on herewith as

Application Serial No. _____

and was amended on _____
(if applicable)

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to the patentability of this application in accordance with Title 37, Code of Federal Regulations, Section 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code, Section 119 of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

Prior Foreign Application(s)

Priority Claimed

(Number) (Country) (Day/Month/Year Filed) Yes ☐ No ☐

I hereby claim the benefit under Title 35, United States Code, Section 119(e) and/or Section 120 of any United States Provisional Application(s) and Nonprovisional Application(s) listed below and, Insofar as the subject matter of each of the claims of the application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code, Section 112, I acknowledge the duty to disclose information material to the patentability of this application as defined in Title 37, Code of Federal Regulations, Section 1.56 which occurred between the filing date of the prior application and the national or PCT international filing date of this application;

(Application Serial No.) (Filing Date) (Status) (patented, pending, abandoned)

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that willful false statements may jeopardize the validity of the application or any patent issued thereon.

POWER OF ATTORNEY: As a named inventor I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and transact all business in the Patent and Trademark Office connected therewith (list name and registration number). The Attorney of Record herein is hereby authorized to insert the Application Number and filing date when received from the United States Patent and Trademark Office.

Manny W. Schecter (Reg. 31,722), Kevin M. Jordan (Reg. 40, 277), Christopher A. Hughes (Reg. 26,914), John E. Hoel (Reg. 26,279), Joseph C. Redmond, Jr. (Reg. 18,753), Douglas W. Cameron (Reg. 31,596), Wan Yee Cheung (Reg. 42,410), Thu Ann Dang (Reg. 41,544), Timothy M. Farrell (Reg. 37,321), Louis P. Herzberg (Reg. 41,500), Derek S. Jennings (Reg. 41,473), Stephen C. Kaufman (Reg. 29, 551), Richard M. Ludwin (Reg. 33,010), Daniel P. Morris (Reg. 32,053), Alison D. Mortinger (Reg. 39,306), Louis J. Percello (Reg. 33,206), Robert M. Trepp (Reg. 25,933), Gail H. Zarick (Reg. 43,303).

Send Correspondence to: George Sai-Halaszi, PhD. (Reg. No. 45,430)
145 Fernwood Drive E. Greenwich, RI 02818

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Express Mail Label: **ER459992766US**

Docket No. YOR920030438US1 Page 2 of 4**DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION****CVD Tantalum compounds for FET gate electrodes**Vijay Narayanan

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Inventor's Signature

Date

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DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION

CVD Tantalum compounds for FET gate electrodes

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Date

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Docket No. YOR920030438US1 Page 3 of 4**DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION****CVD Tantalum compounds for FET gate electrodes**Matthew Warren Copel
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Full name of seventh inventorRoy A. Carruthers
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CitizenshipCyril Cabral, Jr.
Full name of eighth inventorCyril Cabral Jr.
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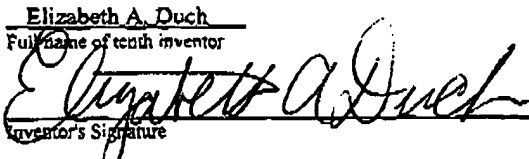
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DK GEORGE SAI-MALMOLZ

Docket No. YOR920030438US1 Page 4 of 4**DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION****CVD Tantalum compounds for FET gate electrodes**Edmund M. Sikorskii
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Docket No. YOR920030438US1 Page 4 of 4**DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION**CVD Tantalum compounds for FET gate electrodesEdmund M. Sikorski

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DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION

CVD Tantalum compounds for FET gate electrodes

Edmund M. Sikorski

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Vijay Narayanan, et al

Date: November 12, 2003

Group Art Unit:

Serial No. : To be assigned

Examiner: To be assigned

Filed: Herewith

Docket No. YOR920030438US1

For: CVD Tantalum compounds for FET gate electrodes

Commissioner for Patents
Alexandria, VA 22313

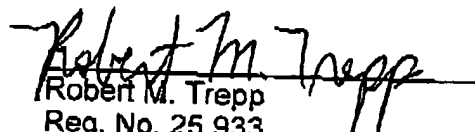
APPOINTMENT OF ASSOCIATE POWER OF ATTORNEY

Sir:

Please recognize George Sai-Halasz, Reg. No. 45,430, of 145 Fernwood Dr., E. Greenwich, RI 02818, T: 401-885-8032 as associate attorney, with full power to prosecute, inspect, and transact all business concerning the above-identified application, including the filing of amendments, continuation applications, divisional applications and continuation-in-part applications.

Please send all official correspondence to George Sai-Halasz to the above noted address.

Respectfully submitted,


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